

METHOD OF MANUFACTURING CODE ADDRESS MEMORY CELL

ABSTRACT OF THE DISCLOSURE

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The present invention relates to a method manufacturing a code address memory (CAM) cell. The present invention uses a dielectric film in which an oxide film and a nitride film between a floating gate and a control gate in a flash memory cell are stacked as a gate insulating film between a semiconductor substrate and a gate in the CAM cell. Therefore, the present invention can reduce the area of a peripheral circuit region and stably secure repaired data since the CAM cell can be stably driven at a low operating voltage and additional boosting circuit is thus not required.